

74HC3G14; 74HCT3G14

Triple inverting Schmitt trigger

Rev. 03 — 8 May 2009

Product data sheet

1. General description

The 74HC3G14; 74HCT3G14 is a high-speed Si-gate CMOS device.

The 74HC3G14; 74HCT3G14 provides three inverting buffers with Schmitt trigger inputs which accept standard input signals. They are capable of transforming slowly changing input signals into sharply defined, jitter-free output signals.

2. Features

- Wide supply voltage range from 2.0 V to 6.0 V
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- Unlimited input rise and fall times
- Multiple package options
- ESD protection:
 - ◆ HBM JESD22-A114E exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
- Specified from -40°C to $+85^{\circ}\text{C}$ and -40°C to $+125^{\circ}\text{C}$

3. Applications

- Wave and pulse shaper for highly noisy environments
- Astable multivibrators
- Monostable multivibrators

4. Ordering information

Table 1. Ordering information

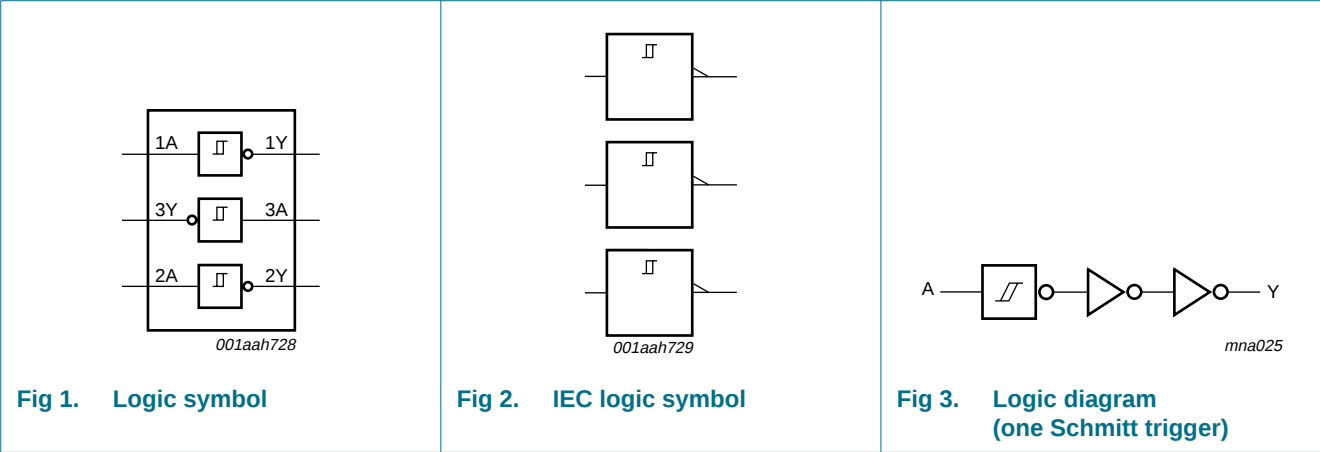
Type number	Package			
	Temperature range	Name	Description	Version
74HC3G14DP 74HCT3G14DP	-40°C to $+125^{\circ}\text{C}$	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2
74HC3G14DC 74HCT3G14DC	-40°C to $+125^{\circ}\text{C}$	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1
74HC3G14GD 74HCT3G14GD	-40°C to $+125^{\circ}\text{C}$	XSON8U	plastic extremely thin small outline package; no leads; 8 terminals; UTLP based; body $3 \times 2 \times 0.5$ mm	SOT996-2

5. Marking

Table 2. Marking

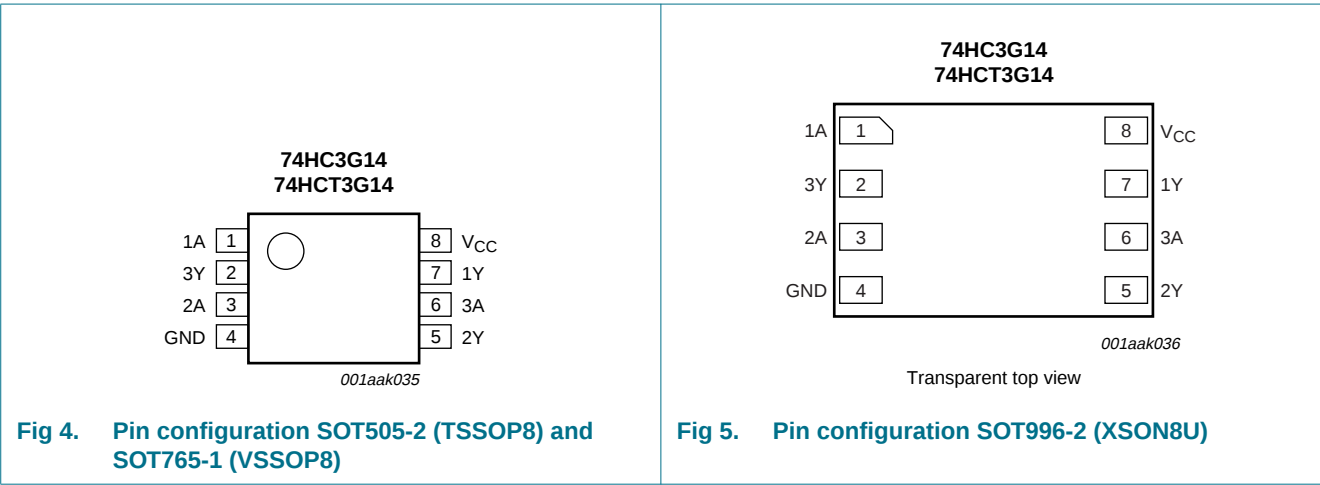
Type number	Marking code
74HC3G14DP	H14
74HCT3G14DP	T14
74HC3G14DC	H14
74HCT3G14DC	T14
74HC3G14GD	H14
74HCT3G14GD	T14

6. Functional diagram



7. Pinning information

7.1 Pinning



7.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
1A, 2A, 3A	1, 3, 6	data input
GND	4	ground (0 V)
1Y, 2Y, 3Y	7, 5, 2	data output
V _{CC}	8	supply voltage

8. Functional description

Table 4. Function table^[1]

Input	Output
nA	nY
L	H
H	L

[1] H = HIGH voltage level; L = LOW voltage level.

9. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+7.0	V
I _{IK}	input clamping current	V _I < -0.5 V or V _I > V _{CC} + 0.5 V	^[1] -	±20	mA
I _{OK}	output clamping current	V _O < -0.5 V or V _O > V _{CC} + 0.5 V	^[1] -	±20	mA
I _O	output current	V _O = -0.5 V to V _{CC} + 0.5 V	^[1] -	±25	mA
I _{CC}	supply current		^[1] -	+50	mA
I _{GND}	ground current		^[1] -50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation		^[2] -	300	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For TSSOP8 package: above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K.
 For VSSOP8 package: above 110 °C the value of P_{tot} derates linearly with 8 mW/K.
 For XSON8U package: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

10. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74HC3G14			74HCT3G14			Unit
			Min	Typ	Max	Min	Typ	Max	
V _{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V _I	input voltage		0	-	V _{CC}	0	-	V _{CC}	V
V _O	output voltage		0	-	V _{CC}	0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C

11. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V). All typical values are measured at T_{amb} = 25 °C.

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	

74HC3G14

V _{OH}	HIGH-level output voltage	V _I = V _{T+} or V _{T-}								
		I _O = -20 µA; V _{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I _O = -20 µA; V _{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = -20 µA; V _{CC} = 6.0 V	5.9	6.0	-	5.9	-	5.9	-	V
		I _O = -4.0 mA; V _{CC} = 4.5 V	4.18	4.32	-	4.13	-	3.7	-	V
		I _O = -5.2 mA; V _{CC} = 6.0 V	5.68	5.81	-	5.63	-	5.2	-	V
V _{OL}	LOW-level output voltage	V _I = V _{T+} or V _{T-}								
		I _O = 20 µA; V _{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 20 µA; V _{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 20 µA; V _{CC} = 6.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 4.0 mA; V _{CC} = 4.5 V	-	0.15	0.26	-	0.33	-	0.4	V
		I _O = 5.2 mA; V _{CC} = 6.0 V	-	0.16	0.26	-	0.33	-	0.4	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 6.0 V	-	-	±0.1	-	±1.0	-	±1.0	µA
I _{CC}	supply current	per input pin; V _{CC} = 6.0 V; V _I = V _{CC} or GND; I _O = 0 A;	-	-	1.0	-	10	-	20	µA
C _I	input capacitance		-	2.0	-	-	-	-	-	pF

74HCT3G14

V _{OH}	HIGH-level output voltage	V _I = V _{T+} or V _{T-}								
		I _O = -20 µA; V _{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = -4.0 mA; V _{CC} = 4.5 V	4.18	4.32	-	4.13	-	3.7	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = 20 µA; V _{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 4.0 mA; V _{CC} = 4.5 V	-	0.15	0.26	-	0.33	-	0.4	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 5.5 V	-	-	±0.1	-	±1.0	-	±1.0	µA

Table 7. Static characteristics ...continued

Voltages are referenced to GND (ground = 0 V). All typical values are measured at $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
I_{CC}	supply current	per input pin; $V_{CC} = 5.5\text{ V}$; $V_I = V_{CC}$ or GND; $I_O = 0\text{ A}$;	-	-	1.0	-	10	-	20	μA
ΔI_{CC}	additional supply current	per input; $V_{CC} = 4.5\text{ V}$ to 5.5 V ; $V_I = V_{CC} - 2.1\text{ V}$; $I_O = 0\text{ A}$	-	-	300	-	375	-	410	μA
C_I	input capacitance		-	2.0	-	-	-	-	-	pF

Table 8. Transfer characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 11](#).

Symbol	Parameter	Conditions	25 °C			–40 °C to +125 °C			Unit
			Min	Typ	Max	Min	Max (85 °C)	Max (125 °C)	

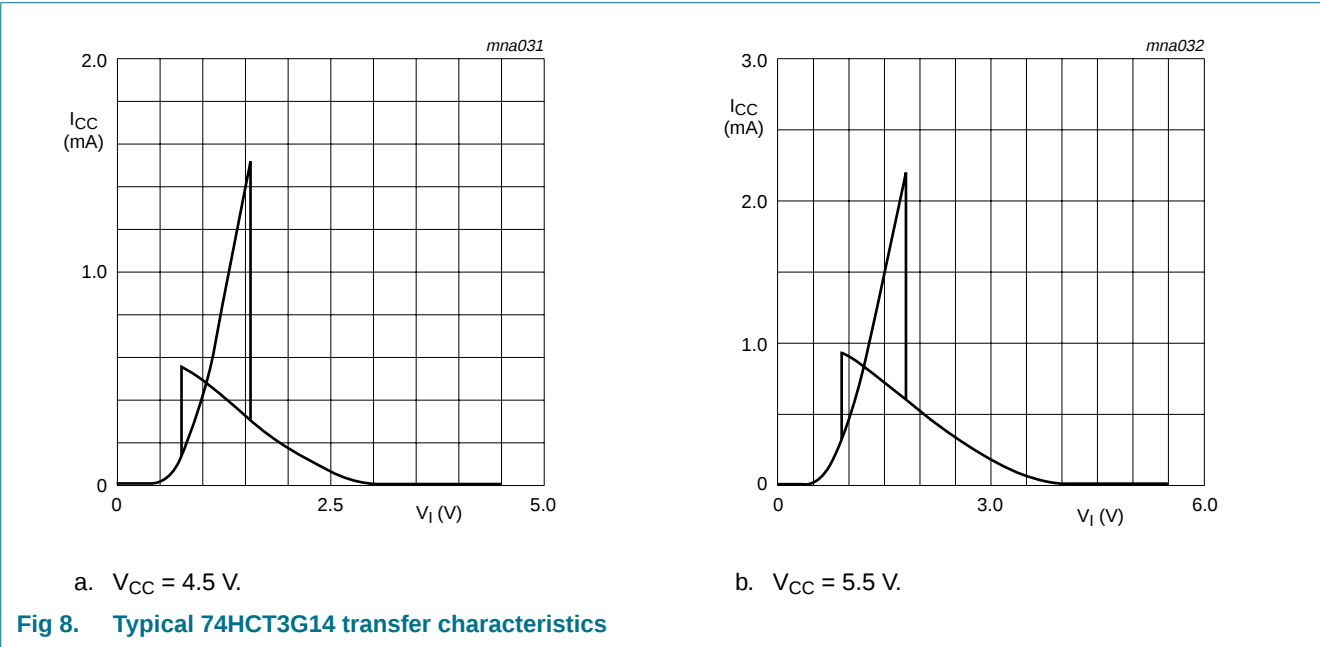
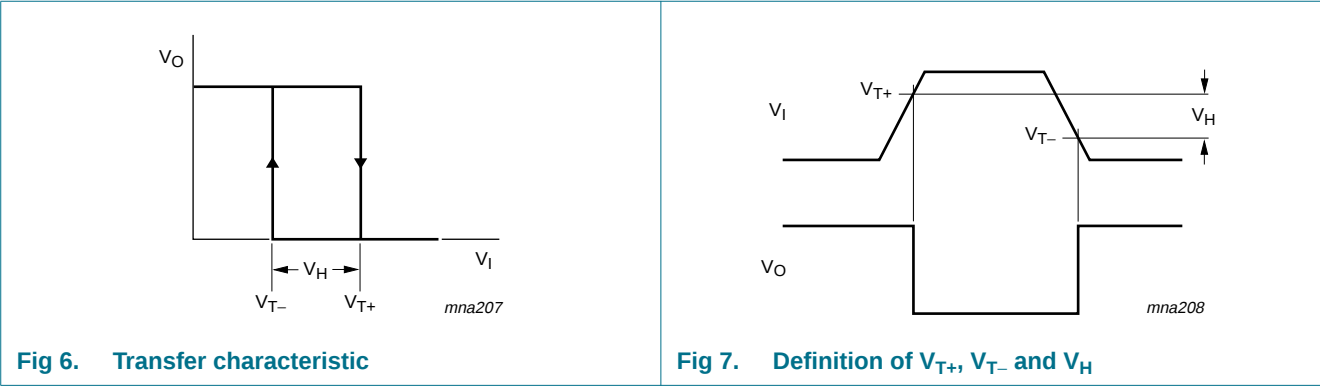
74HC3G14

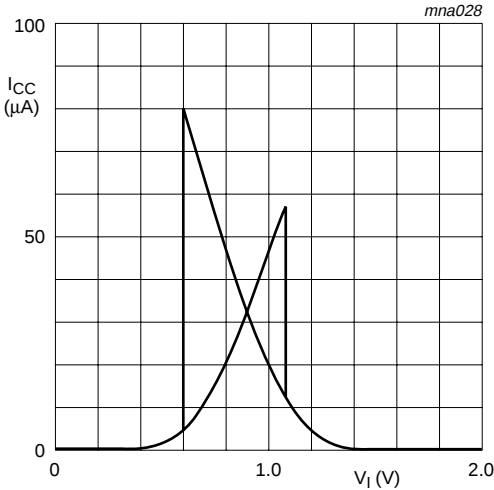
V_{T+}	positive-going threshold voltage	see Figure 6 , Figure 7							
		$V_{CC} = 2.0\text{ V}$	1.00	1.18	1.50	1.00	1.50	1.50	V
		$V_{CC} = 4.5\text{ V}$	2.30	2.60	3.15	2.30	3.15	3.15	V
		$V_{CC} = 6.0\text{ V}$	3.00	3.46	4.20	3.00	4.20	4.20	V
V_{T-}	negative-going threshold voltage	see Figure 6 , Figure 7							
		$V_{CC} = 2.0\text{ V}$	0.30	0.60	0.90	0.30	0.90	0.90	V
		$V_{CC} = 4.5\text{ V}$	1.13	1.47	2.00	1.13	2.00	2.00	V
		$V_{CC} = 6.0\text{ V}$	1.50	2.06	2.60	1.50	2.60	2.60	V
V_H	hysteresis voltage	$(V_{T+} - V_{T-})$; see Figure 6 , Figure 7 and Figure 9							
		$V_{CC} = 2.0\text{ V}$	0.30	0.60	1.00	0.30	1.00	1.00	V
		$V_{CC} = 4.5\text{ V}$	0.60	1.13	1.40	0.60	1.40	1.40	V
		$V_{CC} = 6.0\text{ V}$	0.80	1.40	1.70	0.80	1.70	1.70	V

74HCT3G14

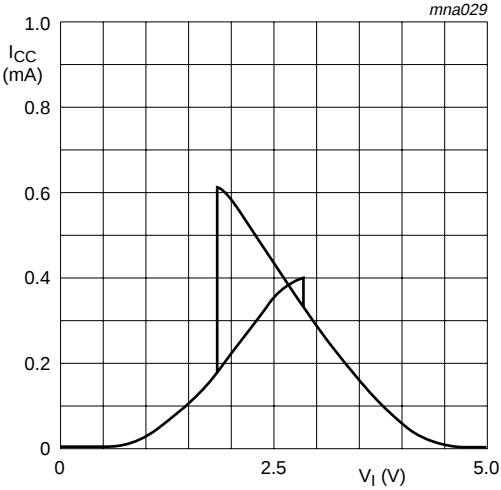
V_{T+}	positive-going threshold voltage	see Figure 6 , Figure 7							
		$V_{CC} = 4.5\text{ V}$	1.20	1.58	1.90	1.20	1.90	1.90	V
		$V_{CC} = 5.5\text{ V}$	1.40	1.78	2.10	1.40	2.10	2.10	V
V_{T-}	negative-going threshold voltage	see Figure 6 , Figure 7							
		$V_{CC} = 4.5\text{ V}$	0.50	0.87	1.20	0.50	1.20	1.20	V
		$V_{CC} = 5.5\text{ V}$	0.60	1.11	1.40	0.60	1.40	1.40	V
V_H	hysteresis voltage	$(V_{T+} - V_{T-})$; see Figure 6 , Figure 7 and Figure 8							
		$V_{CC} = 4.5\text{ V}$	0.40	0.71	-	0.40	-	-	V
		$V_{CC} = 5.5\text{ V}$	0.40	0.67	-	0.40	-	-	V

11.1 Waveforms transfer characteristics

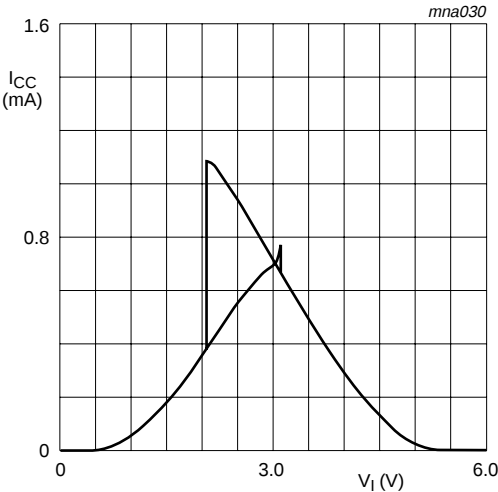




a. $V_{CC} = 2.0 V$



b. $V_{CC} = 4.5 V$



c. $V_{CC} = 6.0 V$

Fig 9. Typical 74HC3G14 transfer characteristics

12. Dynamic characteristics

Table 9. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 11](#).

Symbol	Parameter	Conditions	25 °C			–40 °C to +125 °C			Unit
			Min	Typ	Max	Min	Max (85 °C)	Max (125 °C)	
74HC3G14									
t _{pd}	propagation delay	nA to nY; see Figure 10 [1]							
		V _{CC} = 2.0 V	-	53	125	-	155	190	ns
		V _{CC} = 4.5 V	-	16	25	-	31	38	ns
		V _{CC} = 6.0 V	-	13	21	-	26	32	ns
t _t	transition time	nY; see Figure 10 [2]							
		V _{CC} = 2.0 V	-	20	75	-	95	110	ns
		V _{CC} = 4.5 V	-	7	15	-	19	22	ns
		V _{CC} = 6.0 V	-	5	13	-	16	19	ns
C _{PD}	power dissipation capacitance	V _I = GND to V _{CC} [3]	-	10	-	-	-	-	pF
74HCT3G14									
t _{pd}	propagation delay	nA to nY; see Figure 10 [1]							
		V _{CC} = 4.5 V	-	21	32	-	40	48	ns
t _t	transition time	nY; see Figure 10 [2]							
		V _{CC} = 4.5 V	-	6	15	-	19	22	ns
C _{PD}	power dissipation capacitance	V _I = GND to V _{CC} – 1.5 V [3]	-	10	-	-	-	-	pF

[1] t_{pd} is the same as t_{PLH} and t_{PHL}

[2] t_t is the same as t_{TLH} and t_{THL}

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

13. Waveforms

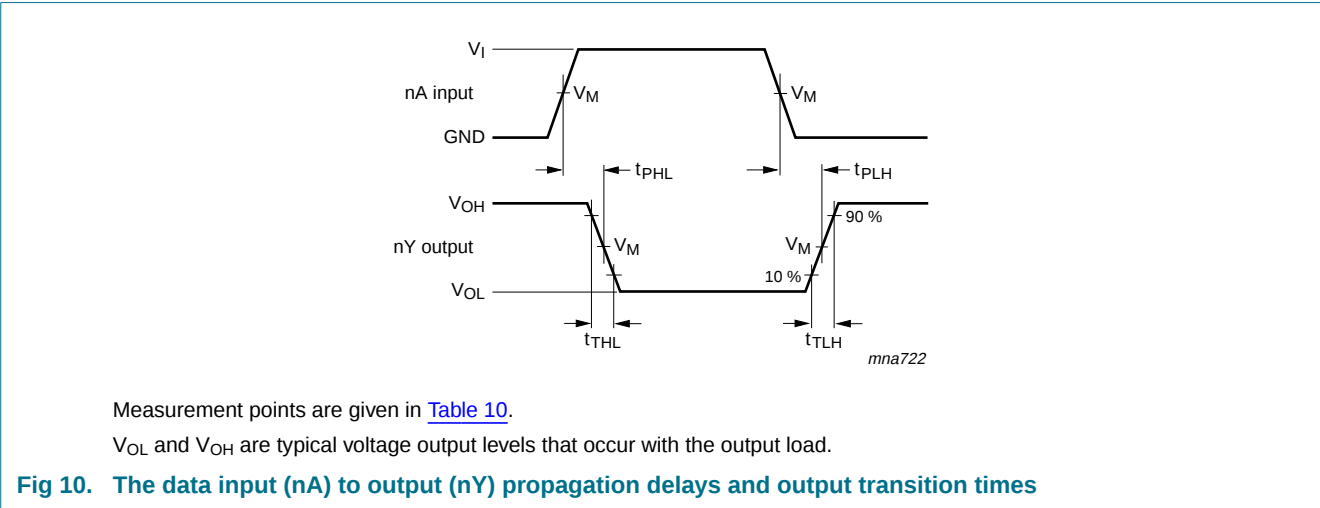


Table 10. Measurement points

Type	Input	Output
	V_M	V_M
74HC3G14	$0.5V_{CC}$	$0.5V_{CC}$
74HCT3G14	1.3 V	1.3 V

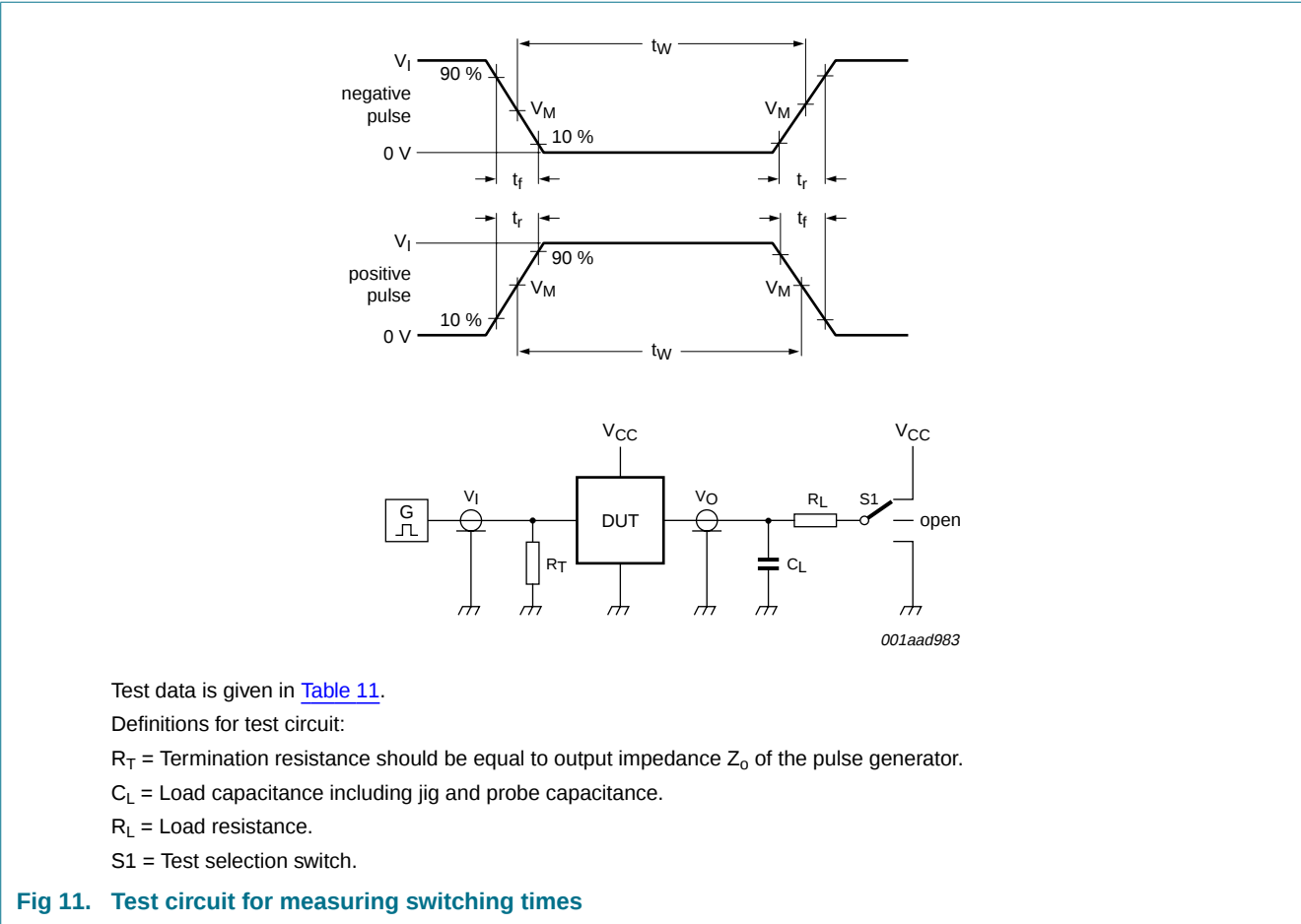


Table 11. Test data

Type	Input		Load		S1 position
	V_I	t_r, t_f	C_L	R_L	t_{PHL}, t_{PLH}
74HC3G14	GND to V_{CC}	≤ 6 ns	50 pF	1 k Ω	open
74HCT3G14	GND to 3.0 V	≤ 6 ns	50 pF	1 k Ω	open

14. Application information

The slow input rise and fall times cause additional power dissipation, which can be calculated using the following formula:

$$P_{\text{add}} = f_i \times (t_r \times \Delta I_{\text{CC(AV)}} + t_f \times \Delta I_{\text{CC(AV)}}) \times V_{\text{CC}} \text{ where:}$$

P_{add} = additional power dissipation (μW);

f_i = input frequency (MHz);

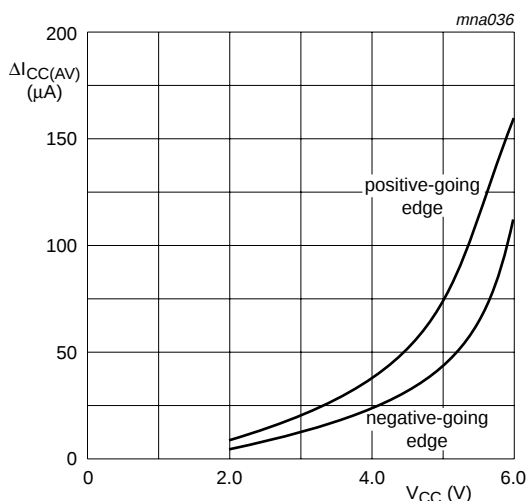
t_r = input rise time (ns); 10 % to 90 %;

t_f = input fall time (ns); 90 % to 10 %;

$\Delta I_{\text{CC(AV)}}$ = average additional supply current (μA).

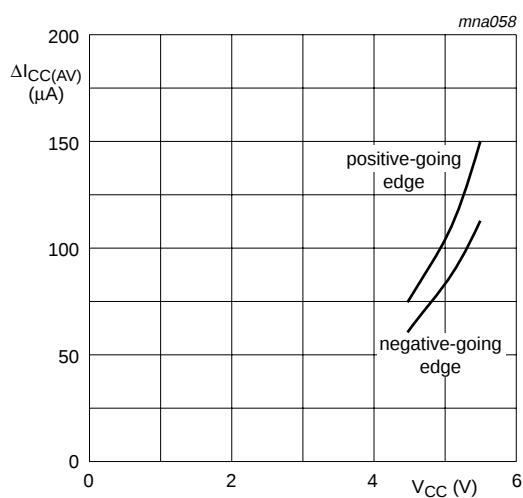
$\Delta I_{\text{CC(AV)}}$ differs with positive or negative input transitions, as shown in [Figure 12](#) and [Figure 13](#).

An example of a relaxation circuit using the 74HC3G14/74HCT3G14 is shown in [Figure 14](#).



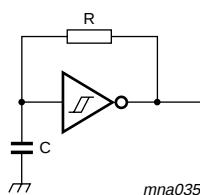
linear change of V_i between $0.1V_{\text{CC}}$ to $0.9V_{\text{CC}}$.

Fig 12. $\Delta I_{\text{CC(AV)}}$ as a function of V_{CC} for 74HC3G14



linear change of V_I between $0.1V_{CC}$ to $0.9V_{CC}$.

Fig 13. $\Delta I_{CC(AV)}$ as a function of V_{CC} for 74HCT3G14



For 74HC3G14: $f = \frac{1}{T} \approx \frac{1}{0.8 \times RC}$

For 74HCT3G14: $f = \frac{1}{T} \approx \frac{1}{0.67 \times RC}$

Fig 14. Relaxation oscillator

15. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2

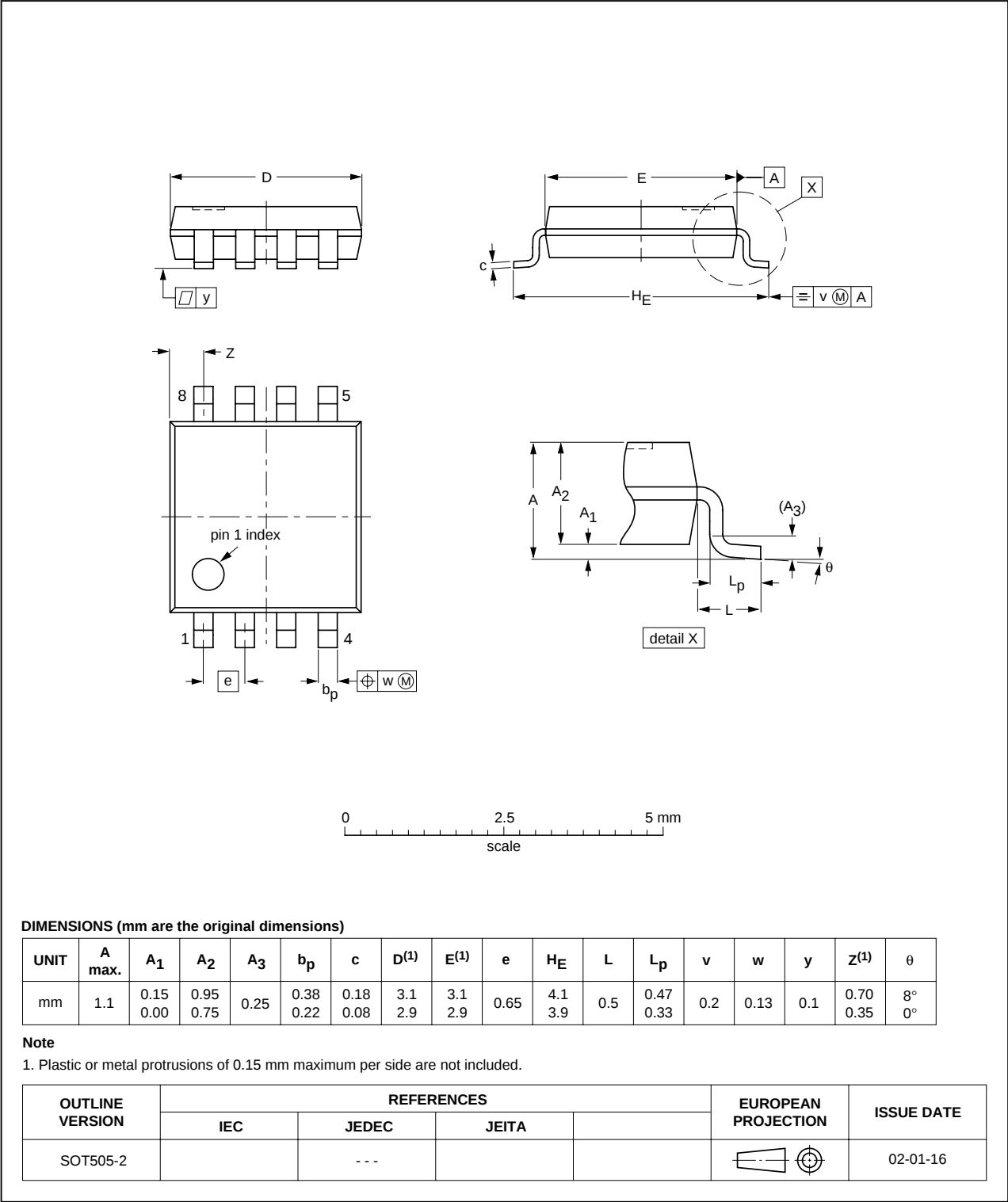


Fig 15. Package outline SOT505-2 (TSSOP8)

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1

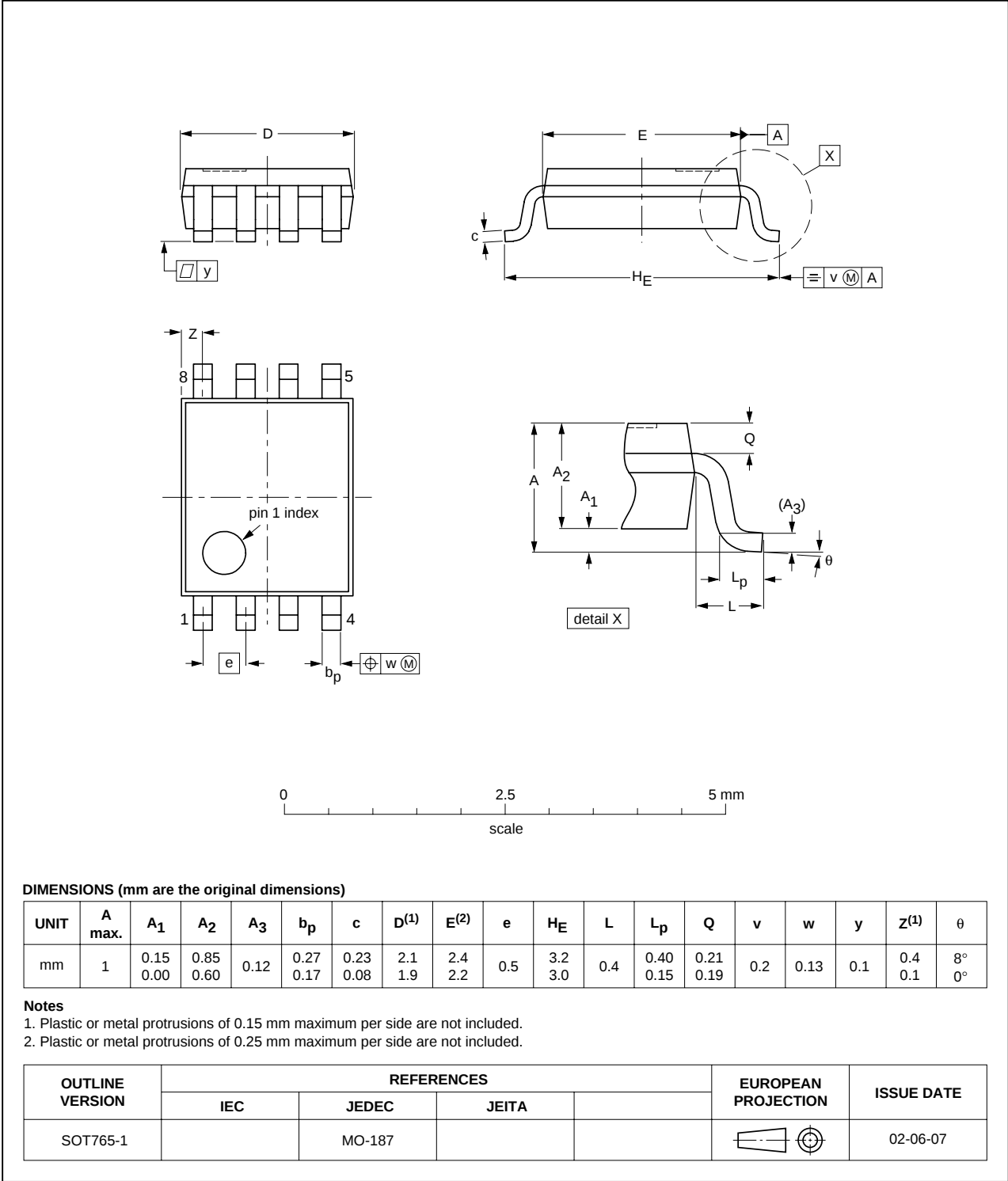


Fig 16. Package outline SOT765-1 (VSSOP8)

XSON8U: plastic extremely thin small outline package; no leads;
8 terminals; UTLP based; body 3 x 2 x 0.5 mm

SOT996-2

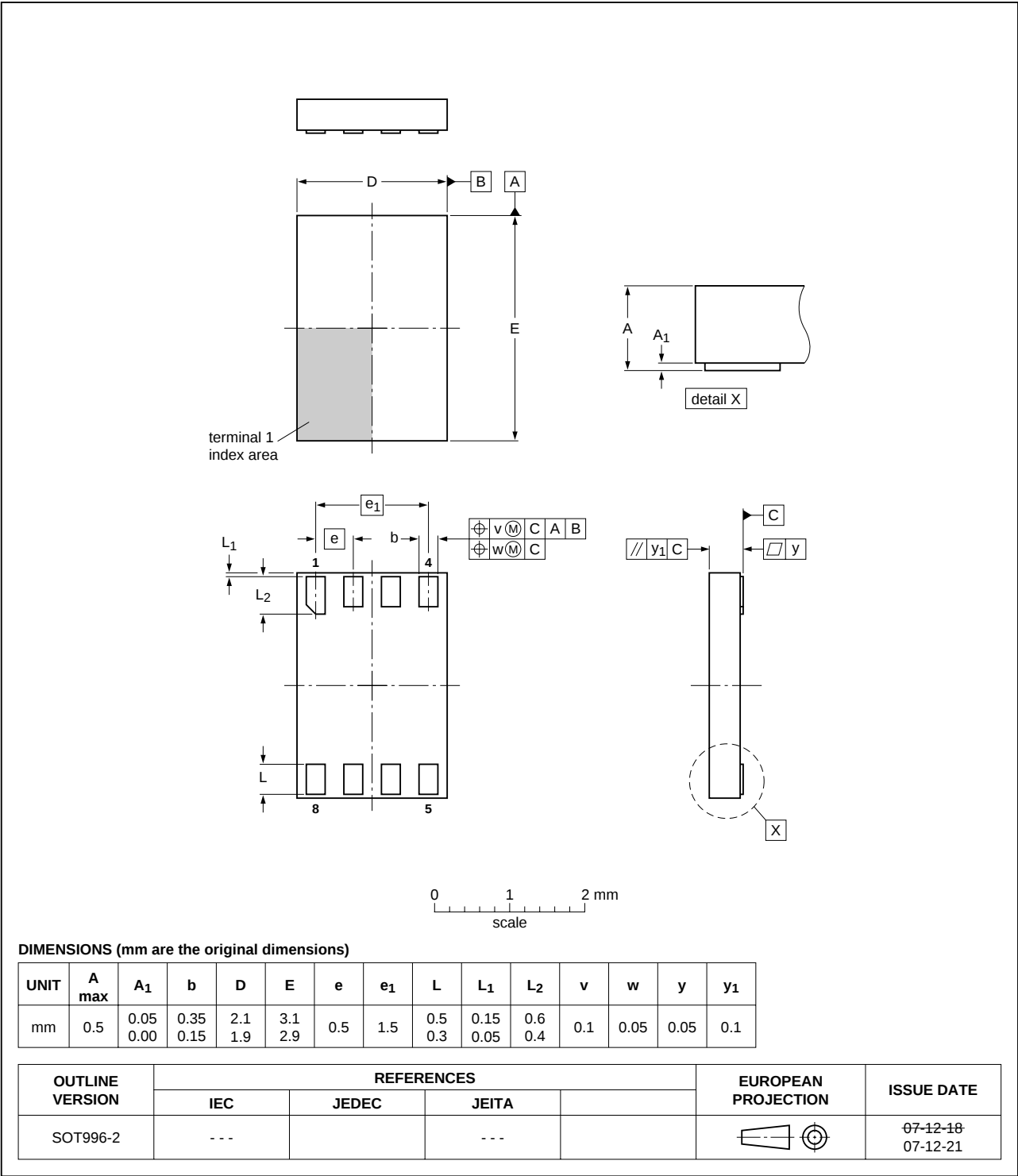


Fig 17. Package outline SOT996-2 (XSON8U)

16. Abbreviations

Table 12. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model

17. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT3G14_3	20090508	Product data sheet	-	74HC_HCT3G14_2
Modifications:	- The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. - Legal texts have been adapted to the new company name where appropriate. - Added type number 74HC3G14GD and 74HCT3G14GD (XSON8U package)			
74HC_HCT3G14_2	20031104	Product specification	-	74HC_HCT3G14_1
74HC_HCT3G14_1	20020723	Product specification	-	-

18. Legal information

18.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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